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P-Channel 40 V (D-S) MOSFEET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
- 40	0.106 at V _{GS} = - 10 V	- 15 ^d			
- 40	0.125 at V _{GS} = - 4.5 V	- 10 ^d			

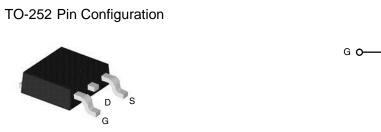
FEATURES

- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested



APPLICATIONS

· Load Switch



Top View

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage		V _{DS}	- 40	V		
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current (T _{.I} = 175 °C)	T _C = 25 °C	- I _D	- 15 ^d			
Continuous Drain Current (1) = 173 C)	T _C = 125 °C		- 10.5			
Pulsed Drain Current	I _{DM}	- 60	Α			
Avalanche Current	I _{AS}	- 15]			
Single Pulse Avalanche Energy ^a	L = 0.1 mH	E _{AS}	51	mJ		
Dower Dissination	T _C = 25 °C	P _D	19 ^c	W		
Power Dissipation	T _A = 25 °C	FD	1.5 ^{b, c}			
Operating Junction and Storage Temperature Range	<u> </u>	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
lunation to Ambient	t ≤ 10 s	- R _{thJA}	40	50	°C/W	
Junction-to-Ambient ^b	Steady State		50	60		
Junction-to-Case		R _{thJC}	0.82	1.1		

Notes:

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



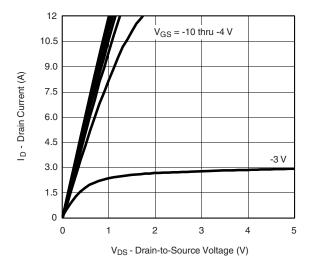
Parameter	Symbol	ol Test Conditions Mi		Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	ource Breakdown Voltage V_{DS} $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 40			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$ -			- 3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 32 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 32 V, V _{GS} = 0 V, T _J = 125 °C			- 50	μΑ	
		$V_{DS} = -32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 ^{\circ}\text{C}$			- 100	1	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 15			Α	
		V _{GS} = - 10 V, I _D = - 5 A		0.106	0.130		
D . O . O D	D	V _{GS} = - 10 V, I _D = - 5 A, T _J = 125 °C			0.145	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 5 A, T _J = 150 °C			0.157	Ω	
		V _{GS} = - 4.5 V, I _D = - 5 A		0.125	0.150		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 5 A		61		S	
Dynamic ^b	•						
Input Capacitance	C _{iss}			1880			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		480		pF	
Reverse Transfer Capacitance	C _{rss}			205			
Total Gate Charge ^c	Q_g			110	165		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -5 \text{ A}$		23		nC	
Gate-Drain Charge ^c	Q _{gd}			18			
Turn-On Delay Time ^c	t _{d(on)}			15	23		
Rise Time ^c	t _r	V_{DD} = - 30 V, R_L = 0.6 Ω		70	105		
Turn-Off Delay Time ^c	t _{d(off)}	$I_{D} = -5 \text{ A}, V_{GEN} = -10 \text{ V}, R_{G} = 6\Omega$		155	235	ns	
Fall Time ^c	t _f]		175	260		
Source-Drain Diode Ratings and Cha	racteristics	T _C = 25 °C ^b					
Continuous Current	I _S				- 15	^	
Pulsed Current	I _{SM}				- 60	Α	
Forward Voltage ^a	V_{SD}	I _F = - 10 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Reverse Recovery Time	ime $t_{rr} = -10 \text{ A}, \frac{dl}{dt} = 100 \text{ A}/\mu \text{s}$			45	70	ns	

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

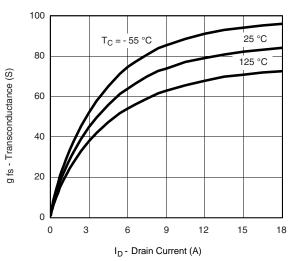
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



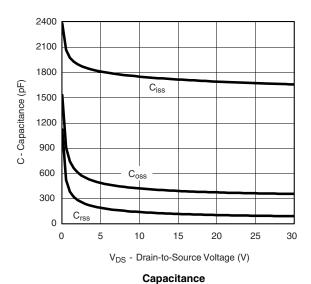
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Output Characteristics

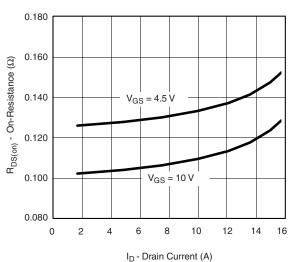


Transconductance

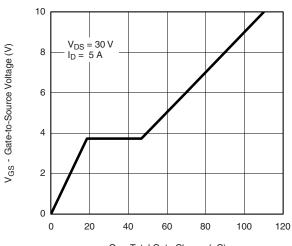


10.5 9.0 I_D - Drain Current (A) 7.5 6.0 4.5 T_C = 125 °C 3.0 25 °C 1.5 0.0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0 V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics



On-Resistance vs. Drain Current

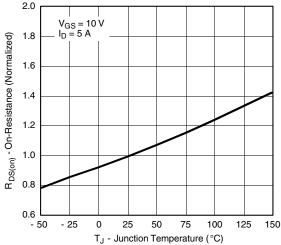


 $\mathbf{Q}_{\mathbf{g}}$ - Total Gate Charge (nC)

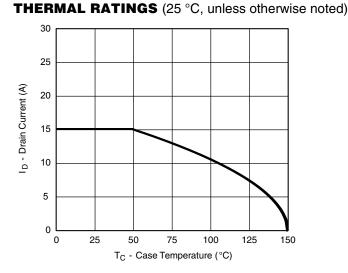
Gate Charge



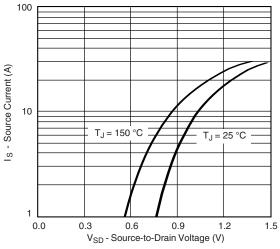
TYPICAL CHARACTERISTICS



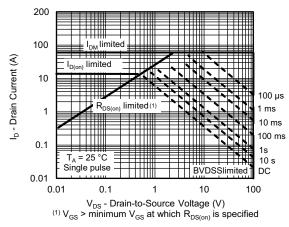
On-Resistance vs. Junction Temperature



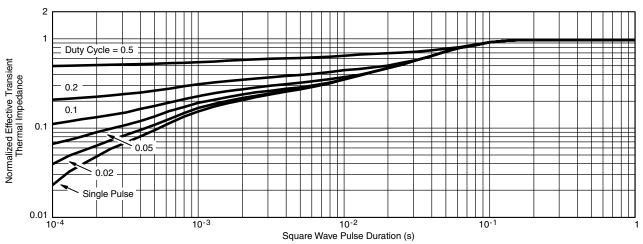
Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage



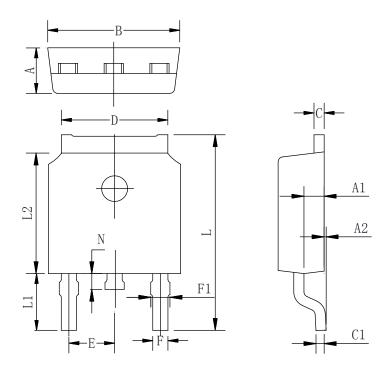
Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
С	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	

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